

IN THE CLAIMS:

Listing of claims:

1. (original) A method for forming an air bearing surface on a slider, comprising,  
providing a silicon slider body;  
forming at least one trench in a surface of the silicon body; and  
forming a structure selected from the group consisting of a carbide structure and a nitride  
structure in the at least one trench.
2. (previously presented) A method as in claim 1, wherein the structure comprises the  
carbide structure.
3. (original) A method as in claim 1, further comprising forming at least one of a read  
element and a write element on the surface after forming the structure.
4. (original) A method as in claim 1, further comprising forming a carbon layer over at  
least a portion of the silicon body on the surface of the slider.
5. (original) A method as in claim 1, further comprising forming the trench by etching  
a portion of the silicon body.
6. (original) A method as in claim 2, further comprising forming a layer between the  
silicon body and the carbide structure.
7. (original) A method as in claim 6, wherein the layer comprises a material comprising  
titanium.
8. (original) A method as in claim 6, wherein the layer comprises a material that  
improves adhesion between the carbide and the silicon.

9. (currently amended) A method as in claim 2, wherein the carbide structure is formed by a process comprising:

filling the trench in the silicon body with a metal carbide and anhydrous metal chloride material;

heating the silicon body so that the metal carbide and anhydrous metal chloride material becomes a melt;

after the heating the silicon body, cooling the silicon body to produce a product material from the melt; metal carbide and anhydrous metal chloride material; and

removing chloride material formed from the product material.

10. (original) A method as in claim 9, further comprising, after the heating the silicon body so that the metal carbide and anhydrous metal chloride material becomes a melt, annealing the silicon body for a predetermined time period.

11. (previously presented) A method as in claim 9, wherein the removing chloride material comprises rinsing the surface of the material with at least one liquid selected from the group consisting of water and methanol to remove the chloride material.

12. (original) A method as in claim 9, further comprising planarizing the carbide using a method selected from the group consisting of etching and polishing.

13. (original) A method as in claim 12, further comprising etching the silicon slider body so that the carbide extends outward from the etched silicon slider body.

14. (original) A method as in claim 9, wherein the heating the silicon body comprises heating the metal carbide and anhydrous metal chloride material to a temperature of at least 450°C.

15. (previously presented) A method as in claim 1, wherein the structure comprises the nitride structure.

16-29. (canceled)

30. (new) A method for forming a surface on a slider, comprising,  
providing a silicon slider body;  
forming at least one trench in a surface of the silicon body; and  
forming a structure selected from the group consisting of a carbide structure and a nitride structure in the at least one trench and extending to a position above the surface of the silicon body adjacent to the trench.

31. (new) A method as in claim 30, wherein the structure comprises a carbide structure.

32. (new) A method as in claim 30, wherein the structure comprises a nitride structure.

33. (new) A method as in claim 30, further comprising forming a read/write head on the slider after forming the structure.

34. (new) A method as in claim 31, wherein the carbide structure is formed by a process comprising:

positioning a metal carbide and an anhydrous metal chloride in the trench;  
forming a melt in the trench by heating the metal carbide and the anhydrous metal chloride;  
after the heating, cooling the melt to yield a cooled product material; and  
removing chloride material from the cooled product material.

35. (new) A method as in claim 34, wherein the removing chloride material comprises rinsing the surface of the material with at least one liquid selected from the group consisting of water and methanol.

36. (new) A method as in claim 34, wherein the heating comprises heating the metal carbide and anhydrous metal chloride material to a temperature of at least 450°C.

37. (new) A method as in claim 34, further comprising forming a layer comprising titanium in the trench prior to the positioning a metal carbide and an anhydrous metal chloride in the trench.

38. (new) A method as in claim 9, further comprising forming a layer comprising titanium in the trench prior to the filling the trench in the silicon body with a metal carbide and anhydrous metal chloride material.

39. (new) A method for forming a surface on a slider, comprising,  
providing a silicon slider body;  
forming a plurality of trenches in a surface of the silicon body;  
forming a structure selected from the group consisting of a carbide structure and a nitride structure in each of the trenches;  
planarizing the structures and the surface of the silicon body; and  
etching the silicon body so that the structure extend to a distance above the silicon body.

40. (new) A method as in claim 39, wherein the structure in each of the trenches comprises a carbide structure.

41. (new) A method as in claim 40, wherein the structure in each of the trenches comprises a nitride structure.

42. (new) A method as in claim 39, further comprising forming a read/write head on the slider after forming the structures.